

Abstract

Support ring for supporting a semiconductor wafer
5 composed of monocrystalline silicon during a thermal
treatment, method for the thermal treatment of such a
semiconductor wafer, and thermally treated
semiconductor wafer composed of monocrystalline silicon

10 A support ring for supporting a semiconductor wafer
composed of monocrystalline silicon during a thermal
treatment of the semiconductor wafer, comprising an
outer and an inner lateral surface and a curved surface
15 extending from the outer to the inner lateral surface
and serving for the placement of the semiconductor
wafer with a radius of curvature of not less than
6000 mm and not more than 9000 mm, if the surface is
designed for the placement of a semiconductor wafer
20 having a diameter of 300 mm, or with a radius of
curvature of not less than 9000 mm and not more than
14 000 mm, if the surface is designed for the placement
of a semiconductor wafer having a diameter of 450 mm. A
method for the thermal treatment of such a
25 semiconductor wafer, and a thermally treated
semiconductor wafer composed of monocrystalline
silicon.

Fig. 2